E-beam Lithography

E-beam lithography used for direct-write utilizes an electron beam to expose PMMA which, after developed, produces nano-patterns in a range from 50nm to 100   ms. For gray-scale mask writing, electron beams expose high-energy beam sensitive (HEBS) glass. This machine can even double as a scanning electron microscope.

Picture shows Raith 50: Delivered December 22, 2000. Christened February 7, 2001. Commissioned March 10, 2001